

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## ES3A THRU ES3G

---

Product specification



## Features

- Ideal for surface mount applications
- Easy pick and place
- Built-in strain relief
- Super fast recovery time for high speed switching

## MECHANICAL DATA

- Case: Molded plastic
- Epoxy: UL 94V-0 rate flame retardant
- Metallurgically bonded construction
- Polarity: Color band denotes cathode end
- Mounting position: Any
- Weight: 0.21 grams

## Reference News

PACKAGE OUTLINE	Pin Configuration
	
<b>SMC</b>	

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwise specified.

Single phase half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

P/N(MARK)	ES3A	ES3B	ES3C	ES3D	ES3E	ES3G	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	150	200	300	400	V
Maximum RMS Voltage	35	70	105	140	210	280	V
Maximum DC Blocking Voltage	50	100	150	200	300	400	V
Maximum Average Forward Rectified Current at T <sub>L</sub> =100℃	3.0						A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	100						A
Maximum Instantaneous Forward Voltage at 3.0A	0.95				1.25		V
Maximum DC Reverse Current Ta=25℃	10						μA
at Rated DC Blocking Voltage Ta=100℃	500						μA
Maximum Reverse Recovery Time (Note 1)	35						nS
Typical Junction Capacitance (Note 2)	45						pF
Operating and Storage Temperature Range T <sub>J</sub> , T <sub>STG</sub>	-65——+150						℃

### NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (ES3A THRU ES3G)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

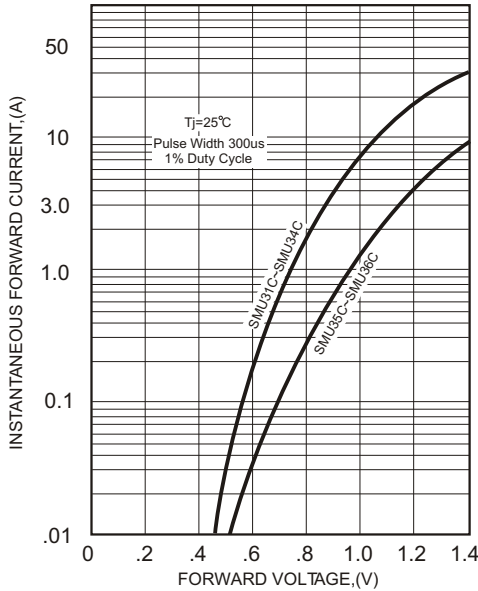


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

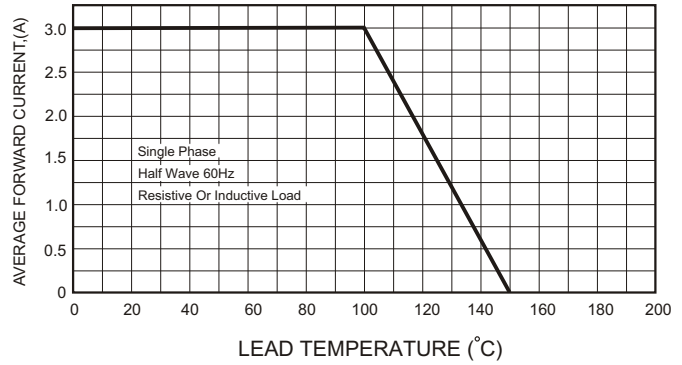


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

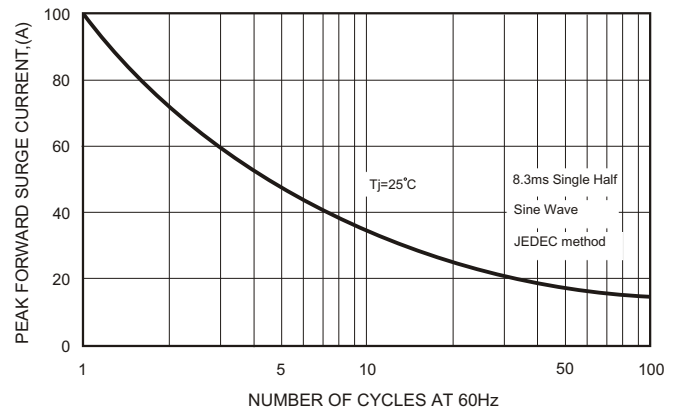
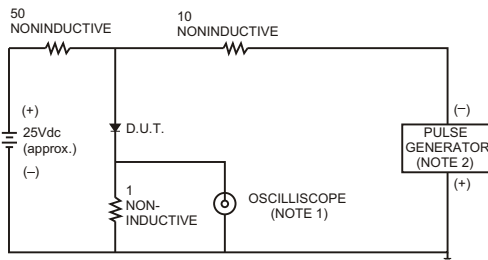


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

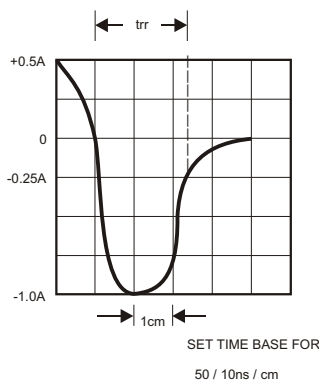
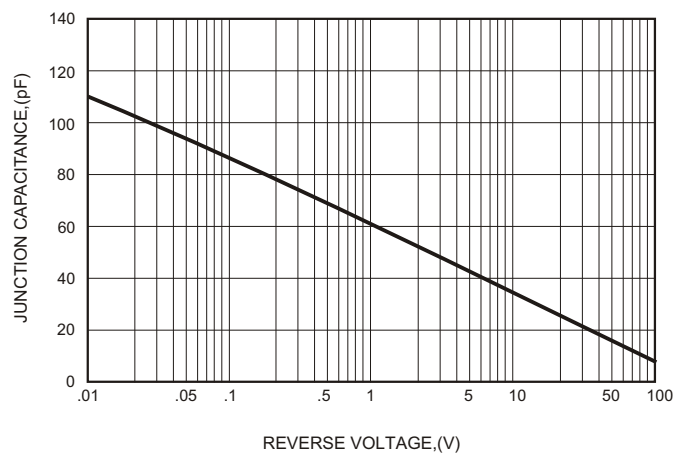
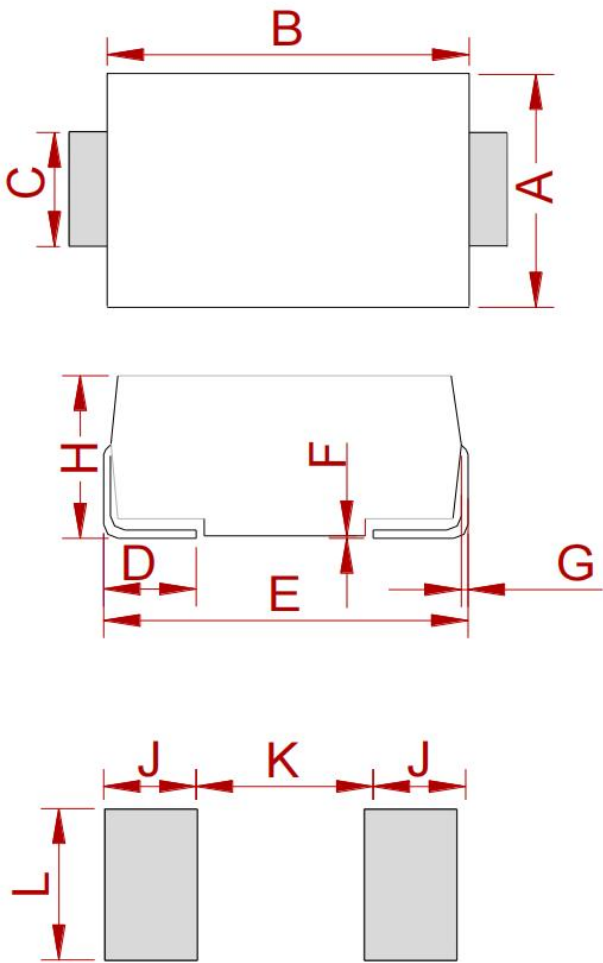


FIG.5-TYPICAL JUNCTION CAPACITANCE



**PACKAGE MECHANICAL DATA**



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	5.75	6.25	0.226	0.246
B	6.90	7.40	0.272	0.291
C	2.75	3.25	0.108	0.128
D	0.95	1.52	0.037	0.060
E	7.70	8.20	0.303	0.323
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
H	2.15	2.62	0.085	0.103
J	2.40		0.094	
K		4.20		0.165
L	3.30		0.130	

DO-214AB (SMC)

**REEL SPECIFICATION**

P/N	PKG	QTY
ES3A THRU ES3G	SMC	3000

## **Attention**

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specification of any and all MSKSEMI Semiconductor products described or contained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.